# **MOSFET** – SiC Power, Single N-Channel, TO247-3L

# 900 V, 20 mΩ, 118 A

# NTHL020N090SC1

#### Features

- Typ.  $R_{DS(on)} = 20 \text{ m}\Omega @ V_{GS} = 15 \text{ V}$
- Typ.  $R_{DS(on)} = 16 \text{ m}\Omega @ V_{GS} = 18 \text{ V}$
- Ultra Low Gate Charge ( $Q_{G(tot)} = 196 \text{ nC}$ )
- Low Effective Output Capacitance (Coss = 296 pF)
- 100% UIL Tested
- RoHS Compliant

#### **Typical Applications**

- UPS
- DC/DC Converter
- Boost Inverter

#### **MAXIMUM RATINGS** (T<sub>J</sub> = $25^{\circ}$ C unless otherwise noted)

Para	Parameter				
Drain-to-Source Volta	Drain-to-Source Voltage				V
Gate-to-Source Voltag	V <sub>GS</sub>	+22/-8	V		
	Recommended Operation Values of Gate – Source Voltage		V <sub>GSop</sub>	+15/-5	V
Continuous Drain Current $R_{\theta JC}$	Steady State	$T_C = 25^{\circ}C$	I <sub>DC</sub>	118	A
Power Dissipation $R_{\theta JC}$			P <sub>DC</sub>	503	W
Continuous Drain Current $R_{\theta JC}$	Steady State	T <sub>C</sub> = 100°C	I <sub>DC</sub>	83	A
Power Dissipation $R_{\theta JC}$			P <sub>DC</sub>	251	W
Pulsed Drain Current (	Note 2)	$T_A = 25^{\circ}C$	I <sub>DM</sub>	472	А
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	–55 to +175	°C	
Source Current (Body	Source Current (Body Diode)				А
Single Pulse Drain-to- gy (I <sub>L</sub> = 23 A <sub>pk</sub> , L = 1 m			E <sub>AS</sub>	264	mJ

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

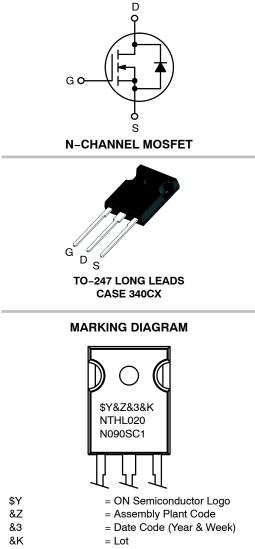
- The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
- 2. Repetitive rating, limited by max junction temperature.
- 3. E<sub>AS</sub> of 162 mJ is based on starting T<sub>J</sub> = 25°C; L = 1 mH, I<sub>AS</sub> = 23 A, V<sub>DD</sub> = 100 V, V<sub>GS</sub> = 15 V.



# **ON Semiconductor®**

#### www.onsemi.com

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> MAX	I <sub>D</sub> MAX
900 V	28 mΩ @ 15 V	118 A



NTHL020N090SC1 = Specific Device Code

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 6 of this data sheet.

#### Table 1. THERMAL CHARACTERISTICS

Parameter	Symbol	Мах	Units
Thermal Resistance Junction-to-Case (Note 1)	$R_{ extsf{ heta}JC}$	0.30	°C/W
Thermal Resistance Junction-to-Ambient (Note 1)	$R_{\theta JA}$	40	°C/W

#### Table 2. ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = $25^{\circ}$ C unless otherwise stated)

Parameter	Symbol	Test C	Condition	Min	Тур	Max	Unit
OFF CHARACTERISTICS					•		
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 V$ , $I_D = 1 mA$		900			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V <sub>(BR)DSS</sub> /T <sub>J</sub>	$I_D = 1 \text{ mA}$ , refer to 25°C			500		mV/°C
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	$T_J = 25^{\circ}C$			100	μA
		V <sub>DS</sub> = 900 V	T <sub>J</sub> = 175°C			250	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = +22/-	-8 V, V <sub>DS</sub> = 0 V			±1	μA
ON CHARACTERISTICS							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>GS</sub> = V <sub>DS</sub>	<sub>S</sub> , I <sub>D</sub> = 20 mA	1.8	2.7	4.3	V
Recommended Gate Voltage	V <sub>GOP</sub>			-5		+15	V
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	$ \begin{array}{c} R_{DS(\text{on})} & \\ & V_{GS} = 15 \; V,  I_D = 60 \; A,  T_J = 25^\circ C \\ \\ & \\ & V_{GS} = 18 \; V,  I_D = 60 \; A,  T_J = 25^\circ C \\ \\ & \\ & V_{GS} = 15 \; V,  I_D = 60 \; A,  T_J = 175^\circ C \end{array} $			20	28	mΩ
					16		
					27		
Forward Transconductance	9 <sub>FS</sub>	$V_{DS} = 20 \text{ V}, \text{ I}_{D} = 60 \text{ A}$			49		S
CHARGES, CAPACITANCES & GATE R	ESISTANCE						
Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> = 0 V, f = 1 MHz,			4415		pF
Output Capacitance	C <sub>OSS</sub>	V <sub>DS</sub>	= 450 V		296		1
Reverse Transfer Capacitance	C <sub>RSS</sub>				24		
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = -5/15	V, V <sub>DS</sub> = 720 V,		196		nC
Threshold Gate Charge	Q <sub>G(TH)</sub>	ID :	= 60 Å		42		
Gate-to-Source Charge	Q <sub>GS</sub>				78		1
Gate-to-Drain Charge	Q <sub>GD</sub>				55		1
Gate-Resistance	R <sub>G</sub>	f = 1 MHz			1.6		Ω
SWITCHING CHARACTERISTICS	ł					•	
Turn-On Delay Time	t <sub>d(ON)</sub>	V <sub>GS</sub> = -5/15	V, V <sub>DS</sub> = 720 V,		40		ns
Rise Time	+	I <sub>D</sub> = 60 A	, R <sub>G</sub> = 2.5 Ω,		63	1	1

Turn–On Delay Time	t <sub>d(ON)</sub>	$V_{GS} = -5/15 \text{ V}, V_{DS} = 720 \text{ V},$	40	ns
Rise Time	t <sub>r</sub>	I <sub>D</sub> = 60 A, R <sub>G</sub> = 2.5 Ω, Inductive Load	63	
Turn-Off Delay Time	t <sub>d(OFF)</sub>		55	
Fall Time	t <sub>f</sub>		13	
Turn–On Switching Loss	E <sub>ON</sub>		2025	Lμ
Turn–Off Switching Loss	E <sub>OFF</sub>		201	
Total Switching Loss	E <sub>TOT</sub>		2226	
	TEDISTICS			

#### DRAIN-SOURCE DIODE CHARACTERISTICS

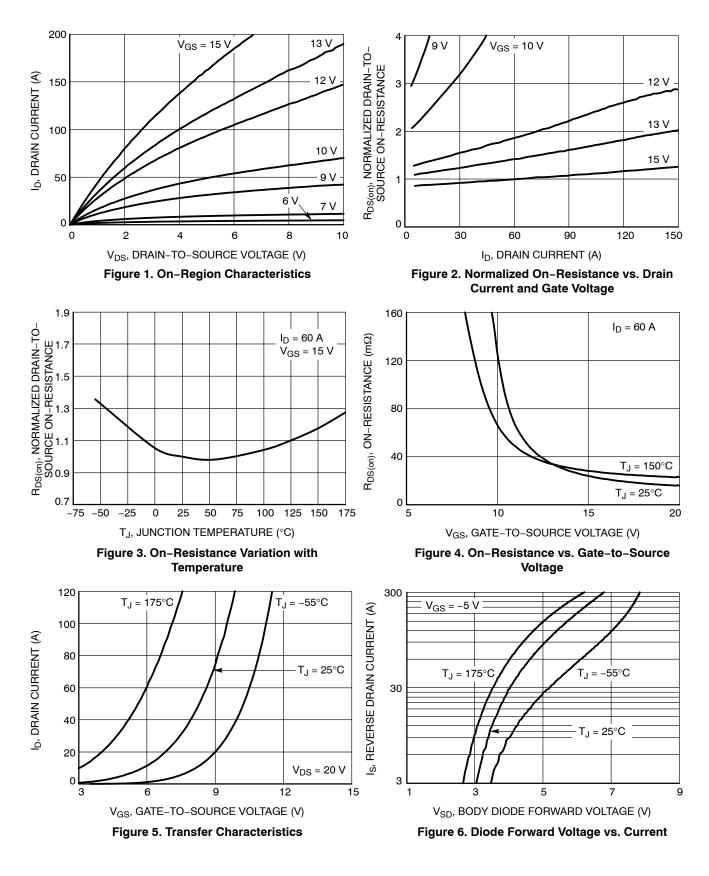
Continuous Drain-Source Diode Forward Current	I <sub>SD</sub>	$V_{GS}$ = -5 V, $T_{J}$ = 25°C		153	A
Pulsed Drain-Source Diode Forward Current (Note 2)	I <sub>SDM</sub>	$V_{GS}$ = -5 V, $T_J$ = 25°C		472	A
Forward Diode Voltage	$V_{SD}$	$V_{GS}$ = –5 V, $I_{SD}$ = 30 A, $T_J$ = 25°C	3.8		V

#### Table 2. ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = $25^{\circ}C$ unless otherwise stated)

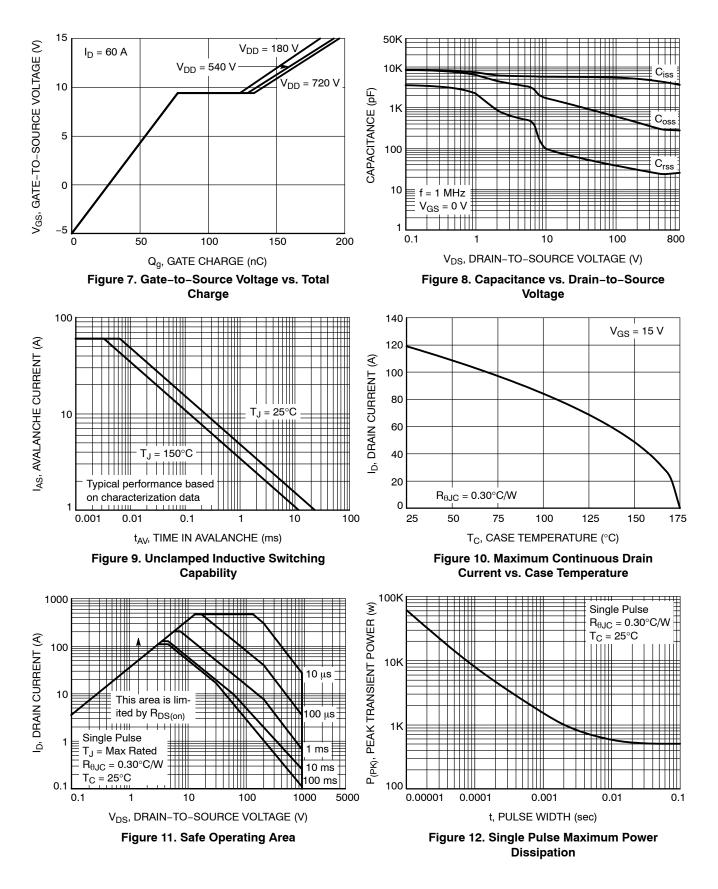
Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
DRAIN-SOURCE DIODE CHARACTER	STICS					
Reverse Recovery Time	t <sub>RR</sub>	$V_{GS} = -5/15 \text{ V}, \text{ I}_{SD} = 60 \text{ A}, \text{ dI}_{S}/\text{dt} =$		28		ns
Reverse Recovery Charge	Q <sub>RR</sub>	1000 Α/μs, V <sub>DS</sub> = 720 V		199		nC
Reverse Recovery Energy	E <sub>REC</sub>			4		μJ
Peak Reverse Recovery Current	I <sub>RRM</sub>	1		14		А
Charge time	Та	1		16		ns
Discharge time	Tb			12		ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

### **TYPICAL CHARACTERISTICS**



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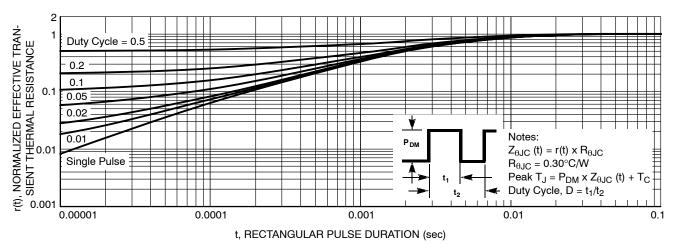
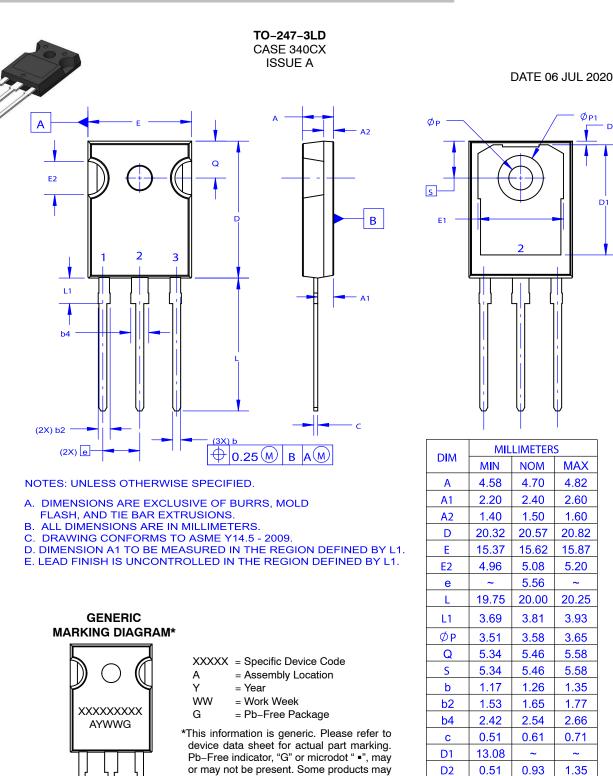


Figure 13. Junction-to-Ambient Transient Thermal Response Curve

#### PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Size	Quantity
NTHL020N090SC1	NTHL020N090SC1	TO-247 Long Lead	Tube	N/A	N/A	30 Units



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